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International Researcher IDs

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Publons / Web Of Science ResearcherID: HOF-0504-2023

Foreign Languages

English, B2 Upper Intermediate

Dissertations

Postgraduate, Yarı-kesikli bir stiren polimerizasyon reaktörünün bulanık kontrol yöntemi ile sıcaklık kontrolü, Gazi University, Fen Bilimleri Enstitüsü, 2009

Research Areas

Physics, Chemistry

Published journal articles indexed by SCI, SSCI, and AHCI

- I. **The investigation of main electrical parameters, energy dependent profiles of surface states and their lifetimes in the Au/n-Si Schottky diodes with (PVA-Fe₃O₄) interlayer depend on frequency and voltage**
YILDIZ K., Khalkhali A., Uzun A., Tanrikulu E. E., Yeriskin S., Alsac A. A.
PHYSICA SCRIPTA, no.1, 2025 (SCI-Expanded)
- II. **The probe of current conduction mechanisms, interface states, and the forward bias intersection point of the Al/Al₂O₃/Ge/p-Si heterostructures depending on temperature**
Akn B., A.Hameed S., ALTINDAL YERİŞKİN S., ULUSOY M., Durmuş H.
Materials Science in Semiconductor Processing, vol.184, 2024 (SCI-Expanded)
- III. **Frequency-dependent dielectric, electric modulus, and ac conductivity features of Au/n-Si Schottky diodes (SDs) with PVC and (PVC:Graphite/Graphene-Oxide) interlayer**
ALTINDAL YERİŞKİN S., Taşcıoğlu İ., BADALI Y.
Journal of Physics D: Applied Physics, vol.57, no.31, 2024 (SCI-Expanded)
- IV. **Enhanced electrical parameters of the Au/n-Si Schottky barrier diodes with graphite/graphene oxide doped PVC interlayer**
Taşcıoğlu İ., BADALI Y., ALTINDAL YERİŞKİN S.
Physica Scripta, vol.99, no.8, 2024 (SCI-Expanded)
- V. **The Electrical and Photodetector Characteristics of the Graphene:PVA/p-Si Schottky Structures Depending on Illumination Intensities**

ULUSOY M., Koçyiğit S., TATAROĞLU A., ALTINDAL YERİŞKİN S.
ACS Omega, vol.9, no.29, pp.32243-32255, 2024 (SCI-Expanded)

- VI. **Quaternary functional semiconductor devices**
ALTINDAL YERİŞKİN S., Dere A., Orman Y., Yakuphanoğlu F.
Physica Scripta, vol.99, no.7, 2024 (SCI-Expanded)
- VII. **Investigation of the interface state characteristics of the Al/Al₂O₃/Ge/p-Si heterostructure over a wide frequency range by capacitance and conductance measurements**
Akin B., ULUSOY M., ALTINDAL YERİŞKİN S.
Materials Science in Semiconductor Processing, vol.170, 2024 (SCI-Expanded)
- VIII. **Origin of frequency and voltage dependent negative dielectric properties in the Al/p-Si Schottky diodes with (Cd_{0.3}Zn_{0.7}O) interfacial layer in the wide range of frequency and voltage**
Delen N., Altındal Yerişkin S., ÖZBAY A., Taşcıoğlu İ.
Physica B: Condensed Matter, vol.665, 2023 (SCI-Expanded)
- IX. **Examination on the current conduction mechanisms of Au/n-Si diodes with ZnO-PVP and ZnO/Ag₂WO₄ -PVP interfacial layers**
Taşcıoğlu I., Pirgholi-Givi G., Yerişkin S., AZIZIAN-KALANDARAGH Y.
Journal of Sol-Gel Science and Technology, vol.107, no.3, pp.536-547, 2023 (SCI-Expanded)
- X. **Analysis of the Current Transport Characteristics (CTCs) in the Au/n-Si Schottky Diodes (SDs) with Al₂O₃ Interfacial Layer over Wide Temperature Range**
Buyukbas-Uluslan A., TATAROĞLU A., Altındal-Yerişkin S.
ECS Journal of Solid State Science and Technology, vol.12, no.8, 2023 (SCI-Expanded)
- XI. **Analysis of the Current Transport Characteristics (CTCs) in the Au/n-Si Schottky Diodes (SDs) with Al₂O₃ Interfacial Layer over Wide Temperature Range**
Buyukbas-Uluslan A., Tataroğlu A., Altındal Yerişkin S.
ECS JOURNAL OF SOLID STATE SCIENCE AND TECHNOLOGY, vol.12, pp.83010, 2023 (SCI-Expanded)
- XII. **Dielectric properties of MS diodes with Ag:ZnO doped PVP interfacial layer depending on voltage and frequency**
Altındal Yerişkin S., ERBİLEN TANRIKULU E., ULUSOY M.
Materials Chemistry and Physics, vol.303, 2023 (SCI-Expanded)
- XIII. **Analysis of admittance measurements of Al/Gr-PVA/p-Si (MPS) structure**
Ata D., Yerişkin S., Tataroğlu A., Balbasi M.
JOURNAL OF PHYSICS AND CHEMISTRY OF SOLIDS, vol.169, 2022 (SCI-Expanded)
- XIV. **On the changes in the dielectric, electric modulus, and ac electrical-conductivity in the Al/(C(29)H(32)O17)/p-Si (MPS) structures in wide range of frequency and voltage**
ERBİLEN TANRIKULU E., Yerişkin S.
PHYSICA B-CONDENSED MATTER, vol.623, 2021 (SCI-Expanded)
- XV. **Electrical parameters of Au/(%1Ni-PVA)/n-Si (MPS) structure: Surface states and their lifetimes**
Cetinkaya H. G., Demirezen S., Yerişkin S.
PHYSICA B-CONDENSED MATTER, vol.621, 2021 (SCI-Expanded)
- XVI. **Frequency and voltage-dependent dielectric spectroscopy characterization of Al/(Coumarin-PVA)/p-Si structures**
DEMİREZEN S., Yerişkin S.
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, vol.32, no.20, pp.25339-25349, 2021 (SCI-Expanded)
- XVII. **Influence of graphene doping rate in PVA organic thin film on the performance of Al/p-Si structure**
Yerişkin S., ŞAFAK ASAR Y.
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, vol.32, no.18, pp.22860-22867, 2021 (SCI-Expanded)
- XVIII. **Complex dielectric, complex electric modulus, and electrical conductivity in Al/(Graphene-PVA)/p-Si (metal-polymer-semiconductor) structures**
Karadas S., Yerişkin S., BALBAŞI M., Azizian-Kalandaragh Y.

Journal of Physics and Chemistry of Solids, vol.148, 2021 (SCI-Expanded)

- XIX. Illumination Dependent Electrical Data Identification of the CdZnO Interlayered Metal-Semiconductor Structures**
Tan S. O., Tascioglu I., Altindal Yeriskin S., Tecimer H., Yakuphanoglu F.
SILICON, no.12, pp.2885-2891, 2020 (SCI-Expanded)
- XX. Dielectric, ac conductivity and electric modulus studies at MPS structure with (Cu₂O)-doped PVA interfacial layer**
Buyukbas-Ulusan A., Yeriskin S., Tataroglu A., Balbasi M., Azizian-Kalandaragh Y.
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, no.5-6, pp.256-260, 2020 (SCI-Expanded)
- XXI. A detailed comparative study on electrical and photovoltaic characteristics of Al/p-Si photodiodes with coumarin-doped PVA interfacial layer: the effect of doping concentration**
DEMIREZEN S., Altindal Yeriskin S.
POLYMER BULLETIN, vol.77, no.1, pp.49-71, 2020 (SCI-Expanded)
- XXII. The effects of (graphene doped-PVA) interlayer on the determinative electrical parameters of the Au/n-Si (MS) structures at room temperature**
Yeriskin S., BALBAŞI M., Orak I.
JOURNAL OF MATERIALS SCIENCE-MATERIALS IN ELECTRONICS, no.18, pp.14040-14048, 2017 (SCI-Expanded)
- XXIII. Temperature and voltage dependence of barrier height and ideality factor in Au/0.07 graphene-doped PVA/n-Si structures**
Yeriskin S., Balbasi M., Demirezen S.
INDIAN JOURNAL OF PHYSICS, no.4, pp.421-430, 2017 (SCI-Expanded)
- XXIV. Frequency and voltage dependence of dielectric properties, complex electric modulus, and electrical conductivity in Au/7% graphene doped-PVA/n-Si (MPS) structures**
Yeriskin S., BALBAŞI M., TATAROĞLU A.
JOURNAL OF APPLIED POLYMER SCIENCE, no.33, 2016 (SCI-Expanded)
- XXV. The investigation of dielectric properties and ac conductivity of Au/GO-doped PrBaCoO nanoceramic/n-Si capacitors using impedance spectroscopy method**
Kaya A., Alialy S., Demirezen S., Balbasi M., Yeriskin S., Aytimur A.
CERAMICS INTERNATIONAL, no.2, pp.3322-3329, 2016 (SCI-Expanded)
- XXVI. Frequency and voltage dependent profile of dielectric properties, electric modulus and ac electrical conductivity in the PrBaCoO nanofiber capacitors**
Demirezen S., Kaya A., Yeriskin S., Balbasi M., Uslu I.
Results in Physics, pp.180-185, 2016 (SCI-Expanded)
- XXVII. Electrical and Dielectric Characteristics of Al/Polyindole Schottky Barrier Diodes. II. Frequency Dependence**
Yeriskin S., ÜNAL H. İ., SARI B.
JOURNAL OF APPLIED POLYMER SCIENCE, no.1, pp.390-396, 2011 (SCI-Expanded)

Articles Published in Other Journals

- I. **On the Voltage Dependent Series Resistance, Interface Traps, and Conduction Mechanisms in the Al/(Ti-doped DLC)/p-Si/Au Schottky Barrier Diodes (SBDs)**
hameed s., BERKÜN Ö., Altindal Yeriskin S.
Gazi University Journal of Science Part A: Engineering and Innovation, vol.11, no.1, pp.235-244, 2024 (Peer-Reviewed Journal)
- II. **Voltage Dependent Profiles of the Surface States and Series Resistance (Rs) in the Al-(Cd:ZnO)-pSi Schottky Diodes (SDs) Utilizing Voltage-Current (IV) Characteristics**
Delen N., Tascioglu I., ALTINDAL YERİŞKİN S., ÖZBAY A.
Gazi University Journal of Science, vol.37, no.1, pp.457-463, 2024 (ESCI)

Metrics

Publication: 29

Citation (WoS): 654

Citation (Scopus): 698

H-Index (WoS): 15

H-Index (Scopus): 16

Non Academic Experience

ÇEVRE VE ŞEHİRCİLİK BAKANLIĞI

GÜLHANE ASKERİ TIP AKADEMİSİ KOMUTANLIĞI